

# PMV50UPE

# 20 V, single P-channel Trench MOSFET

20 July 2012

**Product data sheet** 

### 1. Product profile

#### 1.1 General description

P-channel enhancement mode Field-Effect Transistor (FET) in a small SOT23 (TO-236AB) Surface-Mounted Device (SMD) plastic package using Trench MOSFET technology.

#### 1.2 Features and benefits

- 3 kV ESD protected
- Trench MOSFET technology
- · Low threshold voltage

#### 1.3 Applications

- Relay driver
- High-side loadswitch
- Switching circuits

#### 1.4 Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
V <sub>DS</sub>	drain-source voltage	T <sub>j</sub> = 25 °C		-	-	-20	V
$V_{GS}$	gate-source voltage			-8	-	8	V
I <sub>D</sub>	drain current	$V_{GS} = -4.5 \text{ V}; T_{amb} = 25 \text{ °C}; t \le 5 \text{ s}$	[1]	-	-	-3.7	Α
Static charact	Static characteristics						
R <sub>DSon</sub>	drain-source on-state resistance	$V_{GS}$ = -4.5 V; $I_D$ = -3.2 A; $T_j$ = 25 °C		-	50	66	mΩ

<sup>[1]</sup> Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated, mounting pad for drain 6 cm<sup>2</sup>.



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# 2. Pinning information

Table 2. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	G	gate	<u></u> 3	D I
2	S	source		
3	D	drain	1	G S S 017aaa259

# 3. Ordering information

Table 3. Ordering information

Type number	Package					
	Name	Description	Version			
PMV50UPE	TO-236AB	plastic surface-mounted package; 3 leads	SOT23			

# 4. Marking

Table 4. Marking codes

Type number	Marking code [1]
PMV50UPE	%CZ

<sup>[1] % =</sup> placeholder for manufacturing site code

### 5. Limiting values

Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions		Min	Max	Unit
V <sub>DS</sub>	drain-source voltage	T <sub>j</sub> = 25 °C		-	-20	V
$V_{GS}$	gate-source voltage			-8	8	V
I <sub>D</sub>	drain current	$V_{GS} = -4.5 \text{ V}; T_{amb} = 25 \text{ °C}; t \le 5 \text{ s}$	[1]	-	-3.7	Α
		V <sub>GS</sub> = -4.5 V; T <sub>amb</sub> = 25 °C	[1]	-	-3.2	Α
		V <sub>GS</sub> = -4.5 V; T <sub>amb</sub> = 100 °C	[1]	-	-2	Α
I <sub>DM</sub>	peak drain current	$T_{amb}$ = 25 °C; single pulse; $t_p \le 10$ μs		-	-12.8	Α
P <sub>tot</sub>	total power dissipation	T <sub>amb</sub> = 25 °C	[2]	-	500	mW

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Symbol	Parameter	Conditions		Min	Max	Unit
			[1]	-	955	mW
		T <sub>sp</sub> = 25 °C		-	3570	mW
T <sub>j</sub>	junction temperature			-55	150	°C
T <sub>amb</sub>	ambient temperature			-55	150	°C
T <sub>stg</sub>	storage temperature			-65	150	°C
Source-drai	n diode	1	-			-
I <sub>S</sub>	source current	T <sub>amb</sub> = 25 °C	[1]	-	-1	Α
ESD maxim	um rating		,			
V <sub>ESD</sub>	electrostatic discharge voltage	НВМ	[3]	-	3000	V

- Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated, mounting pad for drain 6 cm<sup>2</sup>.
- [2] Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated and standard footprint.
- [3] Measured between all pins.

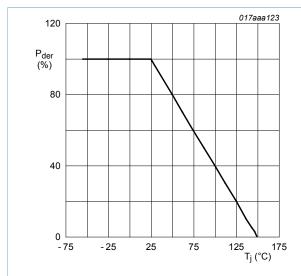


Fig. 1. Normalized total power dissipation as a function of junction temperature

$$P_{der} = \frac{P_{tot}}{P_{tot(25^{\circ}C)}} \times 100 \%$$

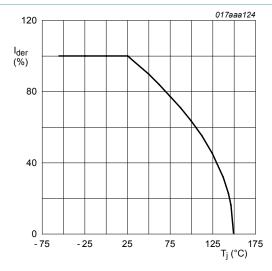


Fig. 2. Normalized continuous drain current as a function of junction temperature

$$I_{der} = \frac{I_D}{I_{D(25^{\circ}\text{C})}} \times 100 \%$$

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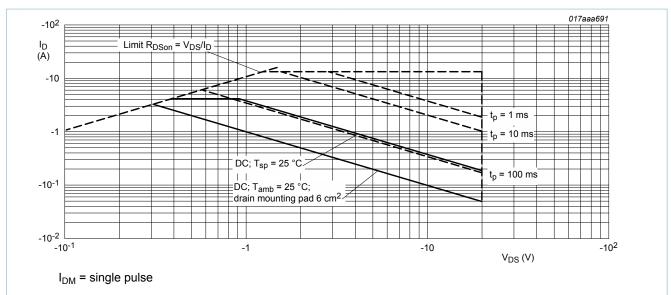


Fig. 3. Safe operating area; junction to ambient; continuous and peak drain currents as a function of drain-source voltage

#### 6. Thermal characteristics

Table 6. Thermal characteristics

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
R <sub>th(j-a)</sub> thermal resistance from junction to ambient			[1]	-	218	250	K/W
	_		[2]	-	114	130	K/W
	ambient		[3]	-	80	92	K/W
R <sub>th(j-sp)</sub>	thermal resistance from junction to solder point			-	30	35	K/W

- [1] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.
- [2] Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for drain 6 cm<sup>2</sup>.
- Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for drain 6 cm<sup>2</sup>,  $t \le 5$  s.

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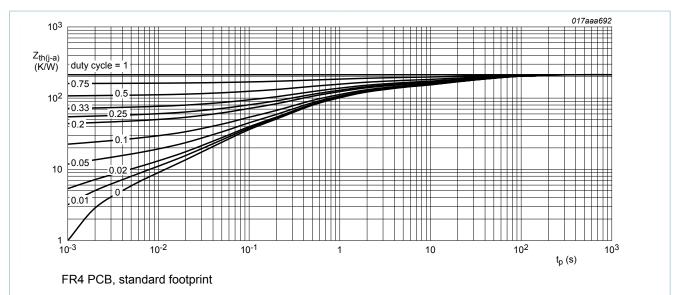


Fig. 4. Transient thermal impedance from junction to ambient as a function of pulse duration; typical values

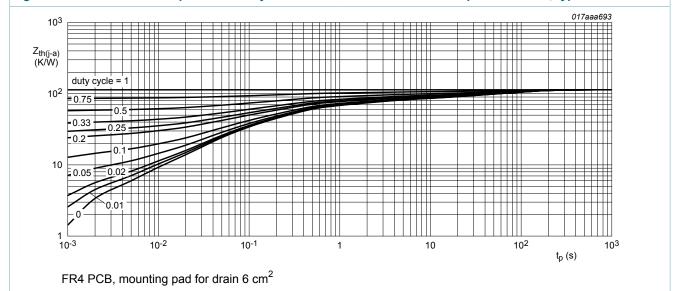


Fig. 5. Transient thermal impedance from junction to ambient as a function of pulse duration; typical values

#### 7. Characteristics

Table 7. Characteristics

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
Static characteristics							
$V_{(BR)DSS}$	drain-source breakdown voltage	$I_D = -250 \mu A; V_{GS} = 0 V; T_j = 25 °C$		-20	-	-	V
$V_{GSth}$	gate-source threshold voltage	$I_D$ = -250 $\mu$ A; $V_{DS}$ = $V_{GS}$ ; $T_j$ = 25 °C		-0.47	-0.6	-0.9	V
I <sub>DSS</sub>	drain leakage current	$V_{DS}$ = -20 V; $V_{GS}$ = 0 V; $T_j$ = 25 °C		-	-	-1	μA
		V <sub>DS</sub> = -20 V; V <sub>GS</sub> = 0 V; T <sub>j</sub> = 150 °C		-	-	-10	μA
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Symbol	Parameter	Conditions		Min	Тур	Max	Unit
I <sub>GSS</sub>	gate leakage current	$V_{GS} = -8 \text{ V}; V_{DS} = 0 \text{ V}; T_j = 25 \text{ °C}$		-	-	10	μA
		V <sub>GS</sub> = 8 V; V <sub>DS</sub> = 0 V; T <sub>j</sub> = 25 °C		-	-	10	μΑ
R <sub>DSon</sub>	drain-source on-state	$V_{GS}$ = -4.5 V; $I_D$ = -3.2 A; $T_j$ = 25 °C		-	50	66	mΩ
	resistance	$V_{GS}$ = -4.5 V; $I_D$ = -3.2 A; $T_j$ = 150 °C		-	73	96	mΩ
		$V_{GS}$ = -2.5 V; $I_D$ = -2.1 A; $T_j$ = 25 °C		-	57	81	mΩ
		$V_{GS}$ = -1.8 V; $I_D$ = -2.1 A; $T_j$ = 25 °C		-	70	110	mΩ
9fs	forward transconductance	$V_{DS}$ = -5 V; $I_{D}$ = -3.2 A; $T_{j}$ = 25 °C		-	18	-	S
Dynamic cl	naracteristics						_
Q <sub>G(tot)</sub>	total gate charge	$V_{DS}$ = -10 V; $I_{D}$ = -3.2 A; $V_{GS}$ = -4.5 V; $T_{j}$ = 25 °C		-	10.5	15.7	nC
Q <sub>GS</sub>	gate-source charge			-	2.2	-	nC
$Q_{GD}$	gate-drain charge			-	2.7	-	nC
C <sub>iss</sub>	input capacitance	V <sub>DS</sub> = -10 V; f = 1 MHz; V <sub>GS</sub> = 0 V;		-	24	-	pF
C <sub>oss</sub>	output capacitance	T <sub>j</sub> = 25 °C		-	106	-	pF
C <sub>rss</sub>	reverse transfer capacitance			-	14.6	-	pF
t <sub>d(on)</sub>	turn-on delay time	$V_{DS}$ = -10 V; $I_{D}$ = -3.2 A; $V_{GS}$ = -4.5 V;		-	400	-	ns
t <sub>r</sub>	rise time	$R_{G(ext)} = 6 \Omega; T_j = 25 °C$		-	700	-	ns
t <sub>d(off)</sub>	turn-off delay time			-	2180	-	ns
t <sub>f</sub>	fall time			-	8800	-	ns
Source-dra	in diode	1	1		1	1	
V <sub>SD</sub>	source-drain voltage	I <sub>S</sub> = -1 A; V <sub>GS</sub> = 0 V; T <sub>j</sub> = 25 °C		-	-0.8	-1.2	V

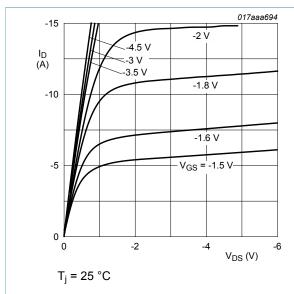


Fig. 6. Output characteristics: drain current as a function of drain-source voltage; typical values

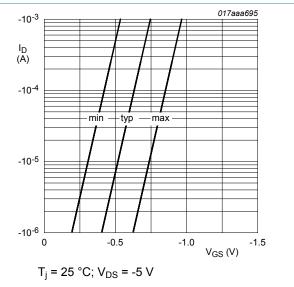


Fig. 7. Sub-threshold drain current as a function of gate-source voltage

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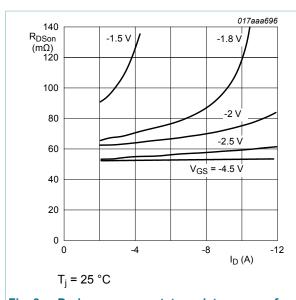


Fig. 8. Drain-source on-state resistance as a function of drain current; typical values

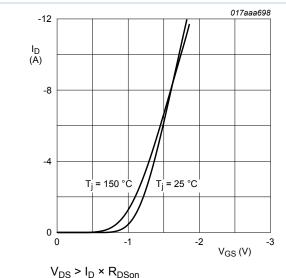


Fig. 10. Transfer characteristics: drain current as a function of gate-source voltage; typical values

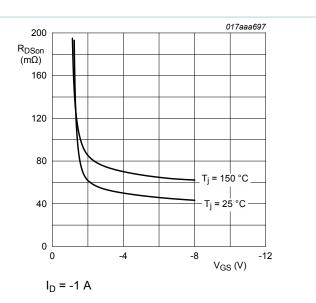


Fig. 9. Drain-source on-state resistance as a function of gate-source voltage; typical values

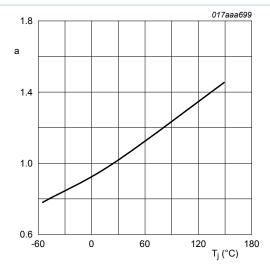


Fig. 11. Normalized drain-source on-state resistance as a function of junction temperature; typical values

$$a = \frac{R_{DSon}}{R_{DSon(25^{\circ}C)}}$$

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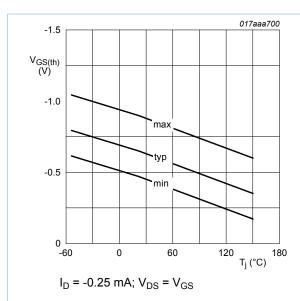


Fig. 12. Gate-source threshold voltage as a function of junction temperature

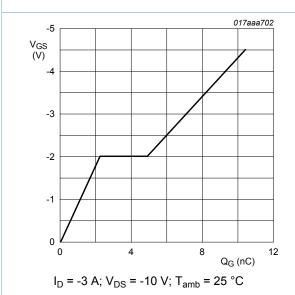


Fig. 14. Gate-source voltage as a function of gate charge; typical values

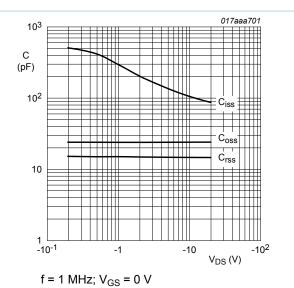


Fig. 13. Input, output and reverse transfer capacitances as a function of drain-source voltage; typical values

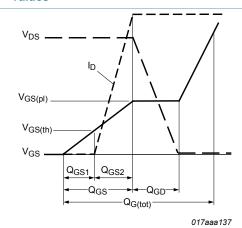
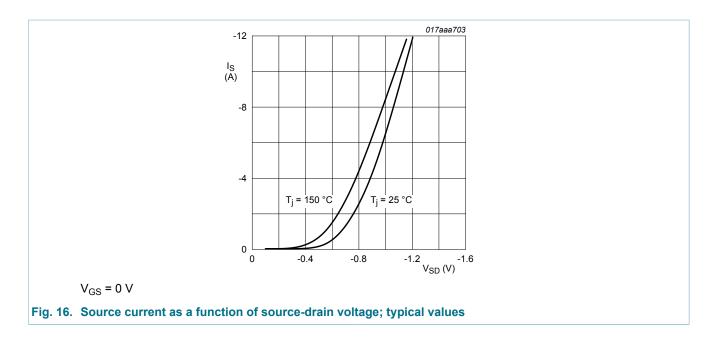
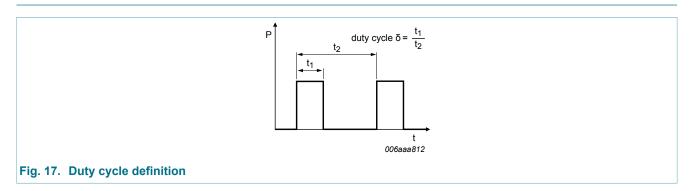


Fig. 15. Gate charge waveform definitions

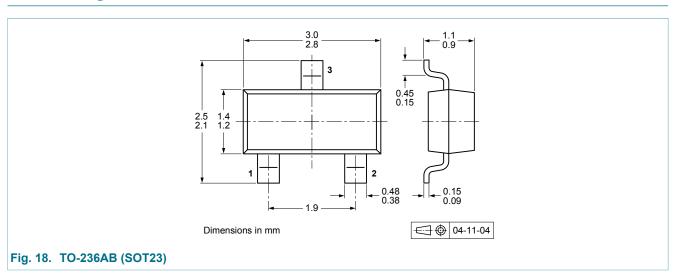
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### 8. Test information



# 9. Package outline

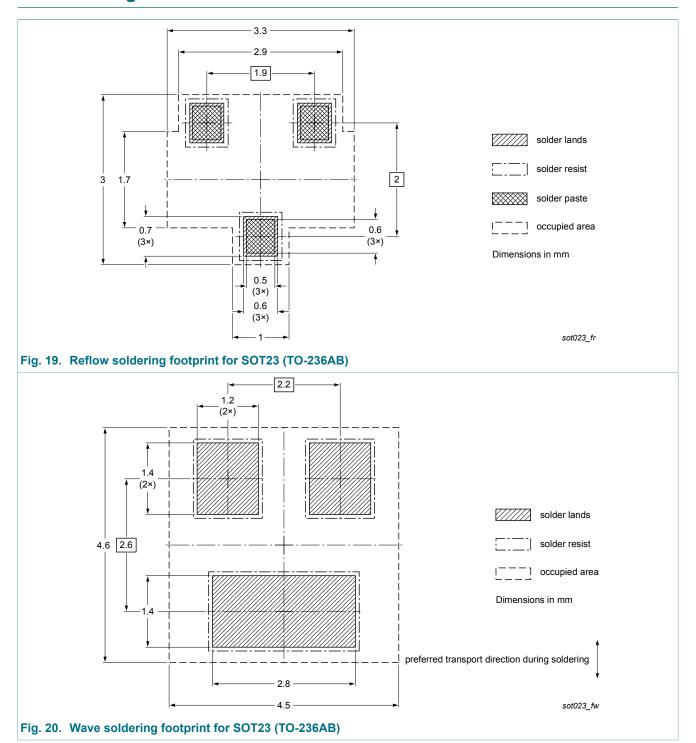


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### 10. Soldering



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# 11. Revision history

#### Table 8. Revision history

Data sheet ID	Release date	Data sheet status	Change notice	Supersedes
PMV50UPE v.1	20120720	Product data sheet	-	-

#### 20 V, single P-channel Trench MOSFET

### 12. Legal information

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Document status [1][2]	Product status [3]	Definition
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